Schedule by Room (I)

Room		Cap.	Sep. 18 (Tue.)		Sep. 19 (Wed.)		Sep. 20 (Thu.)		Sep. 21 (Fri.)	
			AM	PM	AM	PM	AM	PM	AM	PM
Bldg.1	CE (Century Hall)	3000	10:00 ~ 12:00 SP2 Invitation to Informatics	13:00 ~ 18:30 SP2 Invitation to Informatics	09:00 ~ 11:55 S21 JSAP-KPS Joint Symposium: Wide Bandgap Semiconductor Devices	13:00 ~ 14:45 S21 JSAP-KPS Joint Symposium: Wide Bandgap Semiconductor Devices 15:00 ~ 18:45 13.7 Compound and power electron devices and process technology	09:00 ~ 12:15 13.5 Semiconductor devices and related technologies	13:30 ~ 17:45 SP3 Epitaxial Growth and Device Science of GaN	09:00 ~ 11:30 13.5 Semiconductor devices and related technologies	13:30 ~ 17:25 S9 The role of functional oxides in high-frequency devices for IoT
	131 (131+132)	158	09:00 ~ 11:45 10.1 Emerging materials in spintronics and magnetics (including fabrication and charactrization methodologies)	16:00 ~ 17:30 10.1 Emerging materials in spintronics and magnetics (including fabrication and charactrization methodologies)	09:00 ~ 12:00 15.7 Crystal characterization, impurities and crystal defects	13:30 ~ 17:45 15.7 Crystal characterization, impurities and crystal defects	09:00 ~ 12:00 CS.9 Code-sharing Session of 10.1, 10.2, 10.3 & 10.4	13:00 ~ 15:15 CS.9 Code-sharing Session of 10.1, 10.2, 10.3 & 10.4 15:30 ~ 17:00 10.4 Semiconductor spintronics, superconductor, multiferroics	09:00 ~ 12:00 10.4 Semiconductor spintronics, superconductor, multiferroics	13:00 ~ 14:45 10.4 Semiconductor spintronics, superconductor, multiferroics
	133 (133+134)	158		13:30 ~ 17:45 S18 Current status and future prospect of chalcogenide-based thin film solar cells technology	09:00 ~ 12:15 6.1 Ferroelectric thin films	13:45 ~ 19:00 6.1 Ferroelectric thin films	09:30 ~ 11:45 16.3 Bulk, thin-film and other silicon-based solar cells	13:45 ~ 17:45 16.3 Bulk, thin-film and other silicon-based solar cells	09:30 ~ 11:45 16.3 Bulk, thin-film and other silicon-based solar cells	13:45 ~ 17:00 16.3 Bulk, thin-film and other silicon-based solar cells
	135 (135)	72		13:30 ~ 16:00 Tutorial: Jaw-Shen Tsai	09:00 ~ 12:10 Tutorial: Hiroki Kurisu	14:00 ~ 17:30 S1 The manpower training of Science and Technology, education activities and its revitalization - Tokai area -	09:00 ~ 11:30 16.1 Fundamental properties, evaluation, process and devices in disordered materials		09:00 ~ 11:45 13.1 Fundamental properties, surface and interface, and simulations of Si related materials	13:00 ~ 17:15 13.1 Fundamental properties, surface and interface, and simulations of Si related materials
	136 (3F Lobby)	108	09:00 ~ 12:15 3.7 Laser processing	13:45 ~ 18:00 3.7 Laser processing	09:00 ~ 12:15 13.9 Compound solar cells	13:45 ~ 15:45 13.9 Compound solar cells	09:30 ~ 12:00 13.9 Compound solar cells	13:30 ~ 16:15 13.9 Compound solar cells	09:00 ~ 12:15 8.5 Plasma phenomena, emerging area of plasmas and their new applications	13:45 ~ 16:00 8.5 Plasma phenomena, emerging area of plasmas and their new applications
	141 (141+142)	350		13:00 ~ 17:50 SP1 LiDAR for Autonomous Driving	09:00 ~ 10:30 8.1 Plasma production and diagnostics 10:45 ~ 11:45 8.8 Plasma Electronics Award Speech 11:45 ~ 12:15 8.7 Plasma Electronics Invited Talk	13:30 ~ 17:15 S12 Plasma Informatics - Development of Plasma Science by Taking Advantage of Big Data and Analytics	09:00 ~ 12:30 15.6 Group IV Compound Semiconductors (SiC)	13:30 ~ 18:30 S23 Trends of ferroelectric HfO2 technologies	09:00 ~ 12:30 15.6 Group IV Compound Semiconductors (SiC)	13:30 ~ 17:45 S16 Recent Progress of Organic Electronics in Japan and Korea II : from viewpoints of basic science and application
	143 (143)	72	09:30 ~ 11:45 6.6 Probe Microscopy	13:45 ~ 17:45 6.6 Probe Microscopy	09:30 ~ 11:45 6.6 Probe Microscopy	13:45 ~ 17:30 11.1 Fundamental properties	09:30 ~ 11:45 11.1 Fundamental properties	13:45 ~ 17:00 11.2 Thin and thick superconducting films, coated conductors and film crystal growth	09:00 ~ 12:00 CS.6 Code-sharing Session of 3.11 & 13.6	
	144 (4F Lobby)	108		13:00 ~ 18:20 S14 Technological innovation in nanobiology and nanomedicine: from materials, devices to measurement				13:30 ~ 18:35 S22 Renaissance and Novel Development of Poly Si TFT Technology	09:00 ~ 12:30 8.4 Plasma life sciences	
	145 (Reception Hall)	276	09:00 ~ 11:45 12.4 Organic light-emitting devices and organic transistors	13:30 ~ 17:25 S17 Applied physics of metal halide perovskite materials	09:00 ~ 11:45 12.4 Organic light-emitting devices and organic transistors	13:45 ~ 18:00 12.4 Organic light-emitting devices and organic transistors	09:00 ~ 12:15 12.4 Organic light-emitting devices and organic transistors	13:30 ~ 16:35 S6 Quantum computer and Quantum simulater II	09:00 ~ 11:30 13.3 Insulator technology	13:15 ~ 17:00 13.3 Insulator technology
	146 (Reception Hall)	276	09:00 ~ 12:30 15.4 III-V-group nitride crystals	13:30 ~ 18:00 S25 New Process Technology of Nitride Semiconductors	09:00 ~ 12:15 15.4 III-V-group nitride crystals	13:15 ~ 19:15 15.4 III-V-group nitride crystals	09:00 ~ 12:15 15.4 III-V-group nitride crystals	13:45 ~ 16:15 8.4 Plasma life sciences	09:00 ~ 12:15 15.4 III-V-group nitride crystals	13:30 ~ 18:00 15.4 III-V-group nitride crystals
Bldg. 2	211A (211-1)	100		13:15 ~ 18:00 12.3 Functional Materials and Novel Devices	09:00 ~ 11:45 12.3 Functional Materials and Novel Devices	13:15 ~ 14:45 12.3 Functional Materials and Novel Devices	09:15 ~ 12:00 3.6 Ultrashort-pulse and high-intensity lasers	13:15 ~ 18:15 13.6 Nanostructures, quantum phenomena, and nano quantum devices	09:15 ~ 12:15 3.6 Ultrashort-pulse and high-intensity lasers	13:30 ~ 17:15 3.6 Ultrashort-pulse and high-intensity lasers
	211B (211-2)	100	09:15 ~ 11:45 4.1 Plasmonics and Nanophotonics	13:15 ~ 18:15 4.1 Plasmonics and Nanophotonics	09:15 ~ 11:45 4.1 Plasmonics and Nanophotonics	13:15 ~ 18:00 4.1 Plasmonics and Nanophotonics	09:00 ~ 11:45 4.8 Quantum Optics and Nonlinear Optics	13:15 ~ 16:15 4.8 Quantum Optics and Nonlinear Optics	09:00 ~ 11:45 4.2 Photonics Devices, Photonic Integrated Circuit and Silicon Phonics	13:15 ~ 16:15 4.2 Photonics Devices, Photonic Integrated Circuit and Silicon Phonics
	212A (212-1)	100	09:30 ~ 11:45 3.15 Silicon photonics	13:15 ~ 17:30 3.15 Silicon photonics		13:15 ~ 16:30 3.14 Optical control devices and optical fibers		13:15 ~ 17:30 3.9 Terahertz technologies	09:00 ~ 11:45 3.9 Terahertz technologies	13:15 ~ 14:45 3.9 Terahertz technologies
	212B (212-2)	49		13:30 ~ 16:45 CS.8 Code-sharing Session of 7.4 & 9.5	09:15 ~ 12:00 1.3 Novel technologies and interdisciplinary engineering	13:15 ~ 17:15 11.3 Critical Current, Superconducting Power Applications	09:00 ~ 11:00 11.4 Analog applications and their related technologies	13:15 ~ 17:15 11.4 Analog applications and their related technologies	09:00 ~ 12:00 11.5 Junction and circuit fabrication process, digital applications	

Schedule by Room (II)

Room		Cap.	Sep. 18 (Tue.)		Sep. 19 (Wed.)		Sep. 20 (Thu.)		Sep. 21 (Fri.)	
			AM	PM	AM	PM	AM	PM	AM	PM
Bldg. 2	221A (221-1)	49			09:00 ~ 11:45 9.2 Nanowires and Nanoparticles	13:15 ~ 18:15 9.2 Nanowires and Nanoparticles			09:30 ~ 11:30 9.3 Nanoelectronics	13:00 ~ 14:30 9.3 Nanoelectronics
	221B (221-2)	60		13:15 ~ 18:30 4.6 Terahertz Photonics	09:15 ~ 12:00 CS.2 Code-sharing Session of 3.3 & 4.4	13:15 ~ 16:30 CS.2 Code-sharing Session of 3.3 & 4.4		13:15 ~ 17:15 4.5 Nanocarbon and 2D Materials	09:45 ~ 11:45 4.3 Ultrafast Optics and Photonics	13:15 ~ 14:45 4.3 Ultrafast Optics and Photonics
	221C (2F Lounge1)	100	09:00 ~ 11:45 12.7 Biomedical Engineering and Biochips	13:15 ~ 15:30 12.7 Biomedical Engineering and Biochips		13:15 ~ 17:45 12.7 Biomedical Engineering and Biochips	09:00 ~ 11:45 12.7 Biomedical Engineering and Biochips	13:45 ~ 18:00 15.6 Group IV Compound Semiconductors (SiC)		
	222 (222)	108	09:00 ~ 12:00 12.6 Nanobiotechnology	13:30 ~ 17:15 12.6 Nanobiotechnology	09:00 ~ 10:30 12.6 Nanobiotechnology	13:30 ~ 17:00 12.6 Nanobiotechnology	09:00 ~ 12:15 6.3 Oxide electronics	13:15 ~ 19:30 6.2 Carbon-based thin films	09:00 ~ 12:00 6.3 Oxide electronics	13:15 ~ 15:15 7.5 Ion beams
	223 (223)	108	09:15 ~ 11:45 6.3 Oxide electronics	13:15 ~ 18:00 6.3 Oxide electronics	09:00 ~ 12:15 S2 Advances and future prospects of accelerator mass spectrometry	13:45 ~ 16:55 S3 Future research and human resources development using research reactors		13:45 ~ 18:45 S24 Current status and future prospect of atomic layer processes		13:15 ~ 16:30 7.2 Applications and technologies of electron beams
	224A (224-1)	130	11:00 ~ 11:40 Award Ceremony (Exhibition Award, Young Scientist Presentation Award)	15:45~16:30 Representatives Meeting 16:30~18:45 Award Ceremony (Emeritus Members, Paper Award, JSAP Fellows)	09:30 ~ 11:30 21.1 Joint Session K "Wide bandgap oxide semiconductor materials and devices"	13:00 ~ 15:15 21.1 Joint Session K "Wide bandgap oxide semiconductor materials and devices"	09:00 ~ 11:45 3.7 Laser processing	13:15 ~ 18:00 3.12 Nanoscale optical science and near-field optics	09:00 ~ 11:45 3.12 Nanoscale optical science and near-field optics	13:15 ~ 16:45 3.12 Nanoscale optical science and near-field optics
	224B (224-2)	80	09:00 ~ 11:45 17.3 Layered materials	13:15 ~ 16:00 17.3 Layered materials	09:00 ~ 11:45 17.1 Carbon nanotubes & other nanocarbon materials	13:15 ~ 18:45 17.1 Carbon nanotubes & other nanocarbon materials	09:00 ~ 11:45 2.1 Radiation physics and Detector fundamentals	13:30 ~ 15:30 2.1 Radiation physics and Detector fundamentals	09:00 ~ 12:00 2.2 Detection systems	13:00 ~ 15:00 2.2 Detection systems
	225A (225)	42		13:15 ~ 16:30 1.1 Interdisciplinary and General Physics						
	225B (2F Lounge2)	100	09:30 ~ 11:45 3.11 Photonic structures and phenomena		09:00 ~ 11:30 CS.5 Code-sharing Session of 3.11 & 3.13 & 3.15	13:15 ~ 17:15 3.11 Photonic structures and phenomena	09:00 ~ 12:00 CS.4 Code-sharing Session of 3.11 & 3.12	13:30 ~ 16:20 S11 Frontier of Cryo-Electron Microscopy		
	231A (231-1)	49	09:30 ~ 11:45 1.5 Instrumentation, measurement and Metrology	13:15 ~ 17:30 1.5 Instrumentation, measurement and Metrology	09:00 ~ 10:30 16.2 Energy Harvesting	13:15 ~ 15:30 16.1 Fundamental properties, evaluation, process and devices in disordered materials	09:00 ~ 11:45 9.1 Dielectrics, ferroelectrics	13:15 ~ 16:00 1.4 Energy conversion, storage, resources and environment		
	231B (231-2)	60	10:00 ~ 12:00 1.6 Ultrasonics	13:15 ~ 17:45 2.3 Application, radiation generators, new technology		13:15 ~ 16:45 4.7 Laser Material Processing and Manipulation		13:15 ~ 17:15 12.2 Characterization and Materials Physics		
	231C (3F Lounge 1)	100	09:30 ~ 12:15 3.1 Basic optics and frontier of optics	13:15 ~ 18:30 3.1 Basic optics and frontier of optics	09:00 ~ 11:45 12.1 Fabrications and Structure Controls	13:15 ~ 18:15 12.1 Fabrications and Structure Controls	10:00 ~ 12:00 S15 Frontier of organic semiconductor crystals: Toward the Molecular Science of Quantum Liberated Electrons	13:30 ~ 17:30 S15 Frontier of organic semiconductor crystals: Toward the Molecular Science of Quantum Liberated Electrons	09:00 ~ 12:00 12.2 Characterization and Materials Physics	13:15 ~ 16:00 12.2 Characterization and Materials Physics
	232 (232)	108	09:00 ~ 12:00 3.13 Semiconductor optical devices	13:15 ~ 18:00 3.13 Semiconductor optical devices		13:30 ~ 17:20 S5 Frontier of Photonic Artificial Intelligence	10:00 ~ 11:30 CS.1 Code-sharing Session of 3.2 & 12.3	13:30 ~ 16:45 S7 Innovation and development of new business created by Photonics	09:00 ~ 12:00 6.2 Carbon-based thin films	13:15 ~ 18:00 6.2 Carbon-based thin films
	233 (233)	108	09:30 ~ 12:00 13.4 Si wafer processing /Si based thin film /Interconnect technology/ MEMS/ Integration technology	13:30 ~ 18:30 S4 Ubiquitous Power Lasers	09:00 ~ 12:00 13.4 Si wafer processing /Si based thin film /Interconnect technology/ MEMS/ Integration technology	13:30 ~ 17:50 S19 Create a path of future semiconductor devices by new materials and processes	09:30 ~ 11:45 13.4 Si wafer processing /Si based thin film /Interconnect technology/ MEMS/ Integration technology	13:30 ~ 18:00 S20 Advanced ion microscopy for future nanoelectronics materials and devices	09:00 ~ 12:00 13.4 Si wafer processing /Si based thin film /Interconnect technology/ MEMS/ Integration technology	13:00 ~ 16:45 13.4 Si wafer processing /Si based thin film /Interconnect technology/ MEMS/ Integration technology
	234A (234-1)	130	09:00 ~ 10:15 8.6 Plasma Electronics English Session 10:30 ~ 12:00 8.7 Plasma Electronics Invited Talk 12:00 ~ 12:45 8.6 Plasma Electronics English Session			13:30 ~ 16:15 7.3 Micro/Nano patterning and fabrication	09:00 ~ 12:00 21.1 Joint Session K "Wide bandgap oxide semiconductor materials and devices"	13:30 ~ 18:30 21.1 Joint Session K "Wide bandgap oxide semiconductor materials and devices"	09:00 ~ 11:30 3.4 Biomedical optics	13:15 ~ 17:45 3.4 Biomedical optics
	234B (234-2)	80		13:15 ~ 18:30 15.3 III-V-group epitaxial crystals, Fundamentals of epitaxy	09:15 ~ 11:45 6.4 Thin films and New materials	13:15 ~ 18:30 6.4 Thin films and New materials	09:00 ~ 11:45 22.1 Joint Session M "Phonon Engineering"	13:15 ~ 18:00 22.1 Joint Session M "Phonon Engineering"	09:15 ~ 11:45 6.4 Thin films and New materials	13:15 ~ 15:30 6.4 Thin films and New materials
	235 (3F Lounge 2)	90	09:30 ~ 11:45 15.5 Group IV crystals and alloys	13:15 ~ 17:00 15.5 Group IV crystals and alloys	09:45 ~ 11:30 13.8 Optical properties and light-emitting devices	13:30 ~ 17:00 13.8 Optical properties and light-emitting devices	09:30 ~ 11:30 13.8 Optical properties and light-emitting devices	13:30 ~ 17:30 13.8 Optical properties and light-emitting devices	10:00 ~ 12:00 7.1 X-ray technologies	13:30 ~ 16:45 7.1 X-ray technologies
Bldg. 3	311 (Cascade)	200		19:00 ~ 21:00 Welcome Reception	09:00 ~ 12:15 17.3 Layered materials	13:30 ~ 17:15 S27 Trend of van der Waals heterosturctured devices 17.2 Graphene	09:00 ~ 12:15 17.2 Graphene	13:45 ~ 18:30 17.2 Graphene	09:00 ~ 12:45 17.2 Graphene	
	331 (Int'l Conf. Room)	336		13:30 ~ 17:30 SP4 Innovative Plasma Science and Technology toward Future Society – From Semiconductor to Medicine, Agriculture and Space Exploration –	09:00 ~ 10:30 10.2 Fundamental and exploratory device technologies for spin 10:45 ~ 12:15 10.3 Spin devices, magnetic memories and storages	13:45 ~ 17:00 S13 Recent progress of spintronic materials -2 dimensional systems-	09:00 ~ 12:30 13.7 Compound and power electron devices and process technology	13:45 ~ 17:15 13.7 Compound and power electron devices and process technology	09:00 ~ 12:15 13.7 Compound and power electron devices and process technology	13:45 ~ 16:00 13.7 Compound and power electron devices and process technology

Schedule by Room (III)

Room		Cap.	Sep. 18 (Tue.)		Sep. 19 (Wed.)		Sep. 20 (Thu.)		Sep. 21 (Fri.)	
			AM	PM	AM	PM	AM	PM	AM	PM
Bldg.4	431B (431-2)	56	10:00 ~ 12:15 6.5 Surface Physics, Vacuum	13:45 ~ 17:15 CS.7 Code-sharing Session of 6.5 & 7.6	09:00 ~ 10:30 3.5 Laser system and materials 10:45 ~ 12:00 CS.3 Code-sharing Session of 3.5 & 3.14	13:45 ~ 18:45 3.5 Laser system and materials	09:00 ~ 12:15 10.5 Application of magnetic field	13:45 ~ 17:30 3.3 Information photonics and image engineering	09:00 ~ 12:00 15.1 Bulk crystal growth	13:45 ~ 15:30 15.2 II-VI and related compounds
	432 (432)	180	09:30 ~ 12:00 S8 Solid state ionics devices for super smart society. - From fundamentals to applications in ICT, AI and energy devices -	13:30 ~ 17:30 S8 Solid state ionics devices for super smart society. - From fundamentals to applications in ICT, AI and energy devices -	09:00 ~ 12:15 12.5 Organic solar cells	13:45 ~ 17:30 S10 Recent Progresses and Developments of Si Integrated Circuit Technologies with 3D Integrations	09:00 ~ 12:15 12.5 Organic solar cells	14:00 ~ 18:00 S26 The forefront of silica glass	09:00 ~ 12:15 12.5 Organic solar cells	13:45 ~ 18:00 12.5 Organic solar cells
	436 (436)	47			09:30 ~ 11:45 13.2 Exploratory Materials, Physical Properties, Devices	13:45 ~ 18:45 13.2 Exploratory Materials, Physical Properties, Devices		13:45 ~ 15:45 3.2 Equipment optics and materials		
	437 (437)	47			09:00 ~ 12:30 3.12 Nanoscale optical science and near-field optics	13:45 ~ 18:00 9.5 New functional materials and new phenomena	09:00 ~ 12:00 8.3 Plasma nanotechnology			
	438 (3F_Lounge)	140	09:30 ~ 11:30 3.10 Optical quantum physics and technologies	13:45 ~ 16:45 3.10 Optical quantum physics and technologies	09:00 ~ 12:15 3.8 Optical measurement, instrumentation, and sensor	13:45 ~ 19:00 3.8 Optical measurement, instrumentation, and sensor	09:00 ~ 12:15 8.2 Plasma deposition of thin film, plasma etching and surface treatment	13:45 ~ 19:15 8.2 Plasma deposition of thin film, plasma etching and surface treatment	09:15 ~ 12:00 9.4 Thermoelectric conversion	13:45 ~ 17:45 9.4 Thermoelectric conversion
Event Hall	PA1 ~ PA10	Poster Session		[13:30-15 : 30] 1.6 Ultrasonics 6.4 Thin films and New materials 16.1 Fundamental properties, evaluation, process and devices in disordered materials	[09:30-11 : 30] 1.2 Education 3.1 Basic optics and frontier of optics 3.6 Ultrashort-pulse and high-intensity lasers 3.7 Laser processing 3.10 Optical quantum physics and technologies	[13:30-15 : 30] 1.1 Interdisciplinary and General Physics 1.3 Novel technologies and interdisciplinary engineering 3.15 Silicon photonics 15.4 III-V-group nitride crystals 16.3 Bulk, thin-film and other silicon-based solar cells	[09:30-11 : 30] 7 Beam Technology and Nanofabrication 12.2 Characterization and Materials Physics 13.1 Fundamental properties, surface and interface, and simulations of Si related materials 13.2 Exploratory Materials, Physical Properties, Devices 13.3 Insulator technology 15.7 Crystal characterization, impurities and crystal defects	[13:30-15 : 30] 3.11 Photonic structures and phenomena 12.3 Functional Materials and Novel Devices 12.6 Nanobiotechnology 12.7 Biomedical Engineering and Biochips	[09:30-11 : 30] 3.2 Equipment optics and materials 12.1 Fabrications and Structure Controls 13.8 Optical properties and light-emitting devices	
				[16:00-18 : 00] 3.8 Optical measurement, instrumentation, and sensor 12.4 Organic light-emitting devices and organic transistors 13.7 Compound and power electron devices and process technology		[16:00-18 : 00] 1.5 Instrumentation, measurement and Metrology 3.12 Nanoscale optical science and near-field optics 9.4 Thermoelectric conversion 22 Joint Session M		[16:00-18 : 00] 8.1 Plasma production and diagnostics 8.4 Plasma life sciences 8.5 Plasma phenomena, emerging area of plasmas and their new applications 8.6 Plasma Electronics English Session	
Shirotori Hall	PB1 ~ PB10	Poster Session		[13:30-15 : 30] 10 Spintronics and Magnetics 13.4 Si wafer processing /Si based thin film /Interconnect technology/ MEMS/ Integration technology	[09:30-11 : 30] 9.5 New functional materials and new phenomena 11 Superconductivity	[13:30-15 : 30] 6.3 Oxide electronics 6.5 Surface Physics, Vacuum 6.6 Probe Microscopy 7.6 Atomic/molecular beams and beam-related new technologies	[09:30-11 : 30] 1.4 Energy conversion, storage, resources and environment 3.5 Laser system and materials 3.9 Terahertz technologies 3.13 Semiconductor optical devices 3.14 Optical control devices and optical fibers 4.1 Plasmonics and Nanophotonics 4.2 Photonics Devices, Photonic Integrated Circuit and Silicon Phonics 6.1 Ferroelectric thin films 6.2 Carbon-based thin films CS.2 Code-sharing Session of 3.3 & 4.4	[13:30-15 : 30] 9.1 Dielectrics, ferroelectrics 9.2 Nanowires and Nanoparticles 9.3 Nanoelectronics 12.5 Organic solar cells		[13:30-15 : 30] 8.2 Plasma deposition of thin film, plasma etching and surface treatment 8.3 Plasma nanotechnology 13.5 Semiconductor devices and related technologies 13.6 Nanostructures, quantum phenomena, and nano quantum devices 15.1 Bulk crystal growth 15.6 Group IV Compound Semiconductors (SiC)
				[16:00-18 : 00] 17 Nanocarbon Technology		[16:00-18 : 00] 13.9 Compound solar cells 15.3 III-V-group epitaxial crystals, Fundamentals of epitaxy 15.5 Group IV crystals and alloys 21 Joint Session K		[16:00-18 : 00] 2 Ionizing Radiation 3.4 Biomedical optics		